NSN 5961-00-253-5304

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View Online at https://aerobasegroup.com/nsn/5961-00-253-5304 **Inclosure Material:** Metal **Overall Length:** 1.453 inches **Overall Width:** 0.688 inches **Overall Diameter:** 0.667 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 5.5 breakover voltage, dc **Current Rating Per Characteristic:** 30.00 amperes forward current, average peak **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81205-bacsh1n drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug **Reference Number Differentiating Characteristics:** Selected item in accordance with boeing drawing bacsh1n Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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